

Product Overview

Reflowable Thermal Protection Solutions for Power Electronics Designs in Rugged Environments

TE Reflowable Thermal Protection (RTP) device is a low resistance, robust surface mountable thermal protector. It has a set open temperature and can be installed using reliable, lead-free, Surface Mount Device (SMD) assembly and reflow processes.





KEY FEATURES

- Opens at temperature below critical thermal threshold
- Compatible with up to 3 Pb-free solder reflow processes with peak temperatures up to 260°C
- Low series resistance
- DC interrupt voltage capable
- Robust design for harsh environment tested per stringent qualification specification
- RoHS compliant, lead and halogen free

The RTP device described in this overview can withstand the demanding environmental, life, and reliability requirements of automotive and industrial applications, including shock, vibration, temperature cycling, and humidity exposures. In the field, the RTP device opens if its internal junction exceeds the device's specified open temperature. Temperature increases can have multiple sources, one of which is component failure (i.e. when using power components such as a power FET, capacitor, resistor, triac, etc.). The RTP device open temperature is selected so that the device does not open within normal component operating windows, but it does open in a thermal runaway event and before the melt temperature of typical lead free solders.

To simplify installation, improve reliability, and optimize thermal coupling with the PCB, the RTP device is surface mountable. No special SMD installation is required. Instead, after installation, the RTP device utilizes a one time electronic arming process to become thermally sensitive. Before the arming procedure, the device can go through installation temperatures up to 260°C without going open. After arming, the device will open when the critical junction exceeds the open temperature. Arming can occur during test, or in the field.

APPLICATIONS

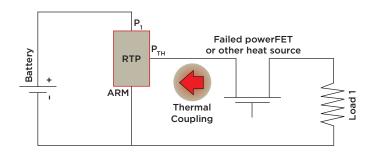
- Helps provide protection against thermal runaway for power FETs and other components if failure occurs in applications such as automotive HVAC, ABS, power steering, DC/DC converters, PTC heaters, etc. or IT servers, telecom power, converters, etc.
- Other DC thermal protection

BENEFITS

- Helps protect the system from thermal runaway damage due to failed power components
- Allows use of standard surface-mount production methods with no special assembly costs
- Low power dissipation and voltage drop
- Supports DC electronic circuits
- Suitable for rugged environment applications (automotive and industrial)
- Green design



TYPICAL APPLICATION BLOCK DIAGRAM

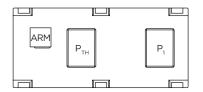


PIN CONFIGURATION & DESCRIPTION PAD LAYOUT RECOMMENDATIONS

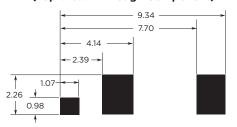
Pin Description

Pin Number	Pin Name	Pin Function
1	P ₁	Power I/O pin (Main power current path)
2	P _{TH}	Thermally sensitive power I/O pin - Intended to share protected component heat sink
3	ARM	Electronic arming pin

Pin Configuration (Bottom View of Device)



Pad Dimensions in mm (Top View – Through Component)



DEFINITION OF TERMS / DEVICE BLOCK DIAGRAM

Junction	The internal interface which must achieve the "Open Temperature" for the RTP device to open thermally after arming. This interface (thermal element) is located directly above the P_{TH} pad.	
Open Temp	The device will open when the junction temperature achieves this value.	
$I_{\mbox{\tiny ARM}}$ and $R_{\mbox{\tiny ARM}}$	Current and resistance levels measured between the ARM pin and either the $\rm P_1$ or $\rm P_{TH}$ pin. These values are relevant only pre device arming.	Thermal Protection Device
$R_{_{PP}}$ and $I_{_{PP}}$	Current and resistance levels measured between the P_1 and P_{TH} pins.	Element ↓ ··· P _{T⊔}



5Ρ.

METHOD OF OPERATION - ELECTRONIC ARMING

The RTP device is a unique thermal protector. It can be reflowed at temperatures up to 260°C without opening, yet in operation it will open at temperatures well below 260°C. To achieve this functionality, the RTP device uses an electronic arming mechanism.

Electronic arming must be done after reflow, and can be done during final test.

The device is armed by sending a specified arming current through the ARM pin of the device. Arming is a time- & current-dependent event. Arming times vs. current are provided in the "Arming Characteristics" section of this overview. Current can flow in either direction through the ARM pin.

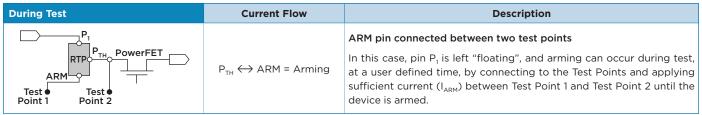
Prior to arming, R_{ARM} should have typical resistance as specified in the "Arming Characteristics" section. Once armed, the ARM pin will be electrically open relative to the P_1 or P_{TH} pins.

Arming has been successful once R_{ARM} exceeds the post-arming minimum resistance specified in the "Arming Characteristics" section. RTP devices must be armed individually and cannot be armed simultaneously in series.

Once "armed", the RTP device will permanently open when the device junction achieves its specified opening temperature.

Although multiple options exist, below is one simple arming option.

Sample Arming Options



ABSOLUTE MAX RATINGS

Abachuta May Datinga	RTP200R060SA	RTP140R060SD	Units	
Absolute Max Ratings	Max	Max		
Max DC Open Voltage (1)	32	32	V _{DC}	
	@ 16 V _{DC}	200	200	
Max DC Interrupt Current 🕦	@ 24 V _{DC}	130	130	А
	@ 32 V _{DC}	100	100	
ESD rating (Human Body Model)	25	25	KV	
Max Reflow Temperature (pre-arming)	260	260	°C	
Operating temperature limits, post-arming, non-opening	-55 +175	-40 +105	°C	

⁽¹⁾ Performance capability at these conditions can be influenced by board design. Performance should be verified in the user's system.



PERFORMANCE CHARACTERISTICS

Resistance and Open Characteristics P_1 to P_{TH}			RTP200R060SA			RTP140R060SD			
			Тур	Max	Min	Тур	Max	Units	
	@ 23+/-3°C	-	0.6	0.8	-	0.7	1.1	mΩ	
$R_{_{PP}}$ (Resistance from $P_{_1}$ to $P_{_{TH}}$)	@ 105+/-3°C	-	-	-	-	0.9	1.2		
	@ 175+/-3°C	-	0.8	1.2	-	-	-		
Operating Voltage	-	-	32	-	-	32	-	V _{DC}	
Open Temperature, post-arming	I _{PP} = O	196	205	213	135	140	145	°C	
Thermal Resistance: Junction to Case	Case = P _{TH} pad	-	0.5	-	-	0.5	-	°C/W	
	@ 23+/-3°C	32	-	-	25	-	-		
Installation dependent Operating Current,	@ 100+/-3°C	27	-	-	_	_	-	A	
post-arming ⁽²⁾⁽³⁾	@ 105+/-3°C	-	-	-	12	_	-		
	@ 175+/-3°C	9	-	-	-	_	-		
Moisture Sensitivity Level Rating (4)	-	-	1	-	-	1	-	-	

ARMING CHARACTERISTICS

Arming Characteristics ARM			RTP200R060SA			RTP140R060SD		
			Тур	Max	Min	Тур	Max	Units
Arming Type			Electronically Armed			Electronically Armed		
	Pre-Arming	-	300	-	-	300	-	mΩ
$R_{_{\!ARM}}$ (Resistance from ARM to $P_{_1}$ or $P_{_{\!TH}})$	Post-Arming	10	-	-	10	-	-	KΩ
Arming Current (I _{ARM}) ⁽²⁾	@ 23 +/-3°C	2	-	5	2	-	5	А
	@ 2A	-	0.10	-	-	0.10	-	Sec
Arming Time (@23 +/-3°C) (2)	@ 5A	-	0.01	-	-	0.01	-	

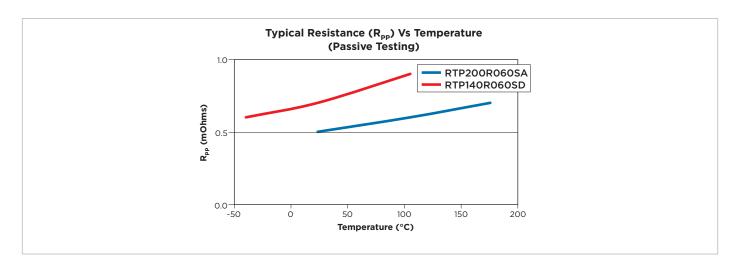
(2) Results were obtained on 44.5 x 57.2 x 1.6 (mm) single layer FR4 boards with 70µm (2oz) Cu traces, and a 645mm², 70µm (2oz) Cu heat spreader connected to the P_{TH} pad of the RTP device. (See RTP device test board drawing) Results will vary based on user's configuration and should be validated by the user in the end system.

⁽³⁾ Operating current is measured on the RTP test boards at the specified temperature. It is a highly installation dependent value.

(4) As per JEDEC J-STD-020C.

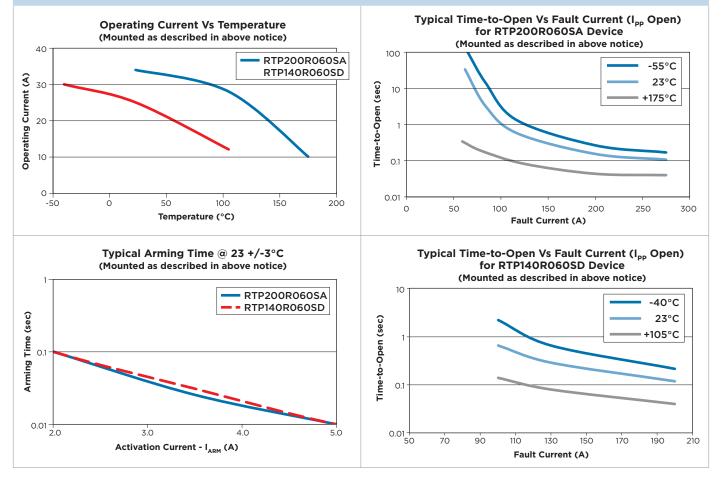


TYPICAL ELECTRICAL PERFORMANCE CHARACTERISTICS

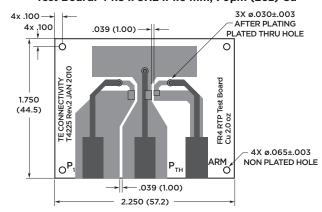


INSTALLATION DEPENDENT PERFORMANCE CHARACTERISTICS

Note: Results were obtained on 44.5 x 57.2 x 1.6 (mm) single layer FR4 boards with 70μm (2oz) Cu traces, and a 645mm², 70μm (2oz)
Cu heat spreader connected to the P_{TH} pad of the RTP device. (See RTP device test board drawing)
Results will vary based on user's configuration and should be validated by the user in the end system.





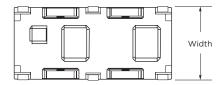


Test Board: 44.5 x 57.2 x 1.6 mm, 70µm (2oz) Cu



MECHANICAL DIMENSIONS

					Length		
	RTP200	R060SA	Linite		4		
	Min	Max	Units				
Height	6.00	6.35	mm	- Height			
Length	11.60	12.00	mm				
Width	5.25	5.50	mm				



MATERIAL CONSTRUCTION



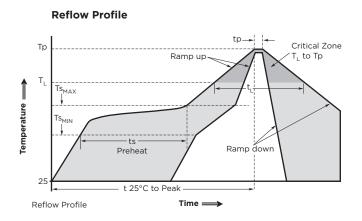
* Halogen Free refers to: Br≤900ppm, Cl≤900ppm, Br+Cl≤1500ppm.



RECOMMENDED REFLOW PROFILE

Classification Reflow Profiles

Profile Feature	Pb-Free Assembly		
Average Ramp-Up Rate (Ts _{MAX} to Tp)	3°C/second max.		
Preheat			
• Temperature Min (Ts _{MIN})	150°C		
• Temperature Max (Ts _{MAX})	200°C		
• Time (ts _{MIN} to ts _{MAX})	60-180 seconds		
Time maintained above:			
• Temperature (T _L)	217°C		
• Time (t _L)	60-150 seconds		
Peak/Classification Temperature (Tp)	260°C		
Time within 5°C of actual Peak Temperature			
Time (tp)	20-40 seconds		
Ramp-Down Rate	6°C/second max.		
Time 25°C to Peak Temperature	8 minutes max.		

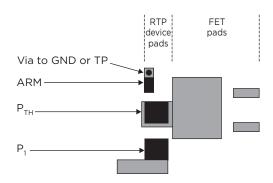


LAYOUT RECOMMENDATIONS

Intimate thermal contact with the potential heat source is critical to achieve the desired protection performance. The RTP device should be used so that the P_{TH} pin shares a copper mounting pad with the primary thermal pin or heat sink of the FET or protected component. Board layout recommendations for appropriate thermal coupling are provided below.

- 1. The RTP device P_{TH} pad must be placed as close to the FET heat sink as practical.
- 2. Connect the P_{TH} pad to the FET heat sink with as thick and wide a copper trace as practical.
- 3. Additional copper layers should NOT be placed directly underneath the P_{TH} pad, and if possible, pull additional copper layers away from the RTP device P_{TH} pad. These additional copper layers work to pull heat away from the RTP device and decrease its thermal sensitivity.
- 4. Pull top layer "cooling" traces as far away from RTP device P_{TH} pad as practical.

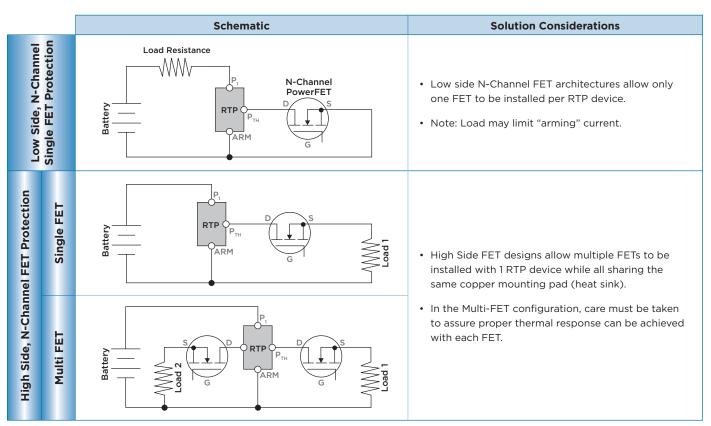
Example layout of an RTP device mounted near to a typical powerFET package on an FR4 type PCB



Note: Thermal conductivity between the RTP device and the heat source is highly dependent on board layout, heat sink structures, and relative placement and design of co-located components. It is the responsibility of the user to verify that the RTP device provides sufficient protection in the user's specific final device implementation.



ALTERNATE & MULTI-FET SCHEMATIC IMPLEMENTATIONS



Note: The degree of thermal connectivity between the heat source and the RTP device is highly dependent on board layouts, PCB material, heat sink structures, and relative placement and design of co-located components. It is the responsibility of the user to verify that the RTP device provides sufficient protection in the user's specific final device implementation.

QUALIFICATION TESTING

The Qualification testing plan for this series of RTP devices is built upon AEC automotive grade testing for ICs (AEC-Q100), discrete semiconductors (AEC-Q101), and passive components (AEC-Q200), with the intent to demonstrate survivability to the most stringent of the relevant requirements.

Contact TE Circuit Protection for updated qualification status and detailed procedures.

*A specific list of tests and conditions is available upon request.

ENVIRONMENTAL SPECIFICATIONS

RTP200R060SA		RTP140R060SD	
Test	Conditions	Test	Conditions
Passive thermal aging	175°C, 1000 hours	Passive aging	105°C, 1000 hours
Active thermal aging	175°C, 3A bias, 1000hr	Humidity aging	85°C, 85% RH, 1000 hours
Passive humidity aging	85°C, 85% RH, 1000 hours	Storage humidity	Per IPC/JEDEC J-STD020A level 1 (MSL1)
Active humidity aging	85°C, 85% RH, 5A bias, 1000hr	Thermal shock	105°C, -40°C (300 times)
Storage humidity	Per IPC/JEDEC J-STD020A level 1 (MSL1)		
Thermal shock	125°C, -55°C (300 times)		



FOR MORE INFORMATION

circuitprotection.com/rtp-launch

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